

74LV164-Q100

8-bit serial-in/parallel-out shift register

Rev. 2 — 18 September 2014

Product data sheet

1. General description

The 74LV164-Q100 is a low-voltage, Si-gate CMOS device and is pin and function compatible with the 74HC164-Q100 and 74HCT164-Q100.

The 74LV164-Q100 is an 8-bit edge-triggered shift register with serial data entry and an output from each of the eight stages. Data is entered serially through one of two inputs (DSA or DSB). Either input can be used as an active HIGH enable for data entry through the other input. Both inputs must be connected together or an unused input must be tied HIGH.

Data shifts one place to the right on each LOW-to-HIGH transition of the clock input (CP). It enters Q0, which is the logical AND-function of the two data inputs (DSA and DSB). Data inputs DSA and DSB, existed one set-up time prior to the rising clock edge.

A LOW on the master reset input (MR) overrides all other inputs and clears the register asynchronously, forcing all outputs LOW.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low-voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7\text{ V}$ and $V_{CC} = 3.6\text{ V}$
- Typical output ground bounce $< 0.8\text{ V}$ at $V_{CC} = 3.3\text{ V}$ and $T_{amb} = 25\text{ }^{\circ}\text{C}$
- Typical HIGH-level output voltage (V_{OH}) undershoot: $> 2\text{ V}$ at $V_{CC} = 3.3\text{ V}$ and $T_{amb} = 25\text{ }^{\circ}\text{C}$
- Gated serial data inputs
- Asynchronous master reset
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)

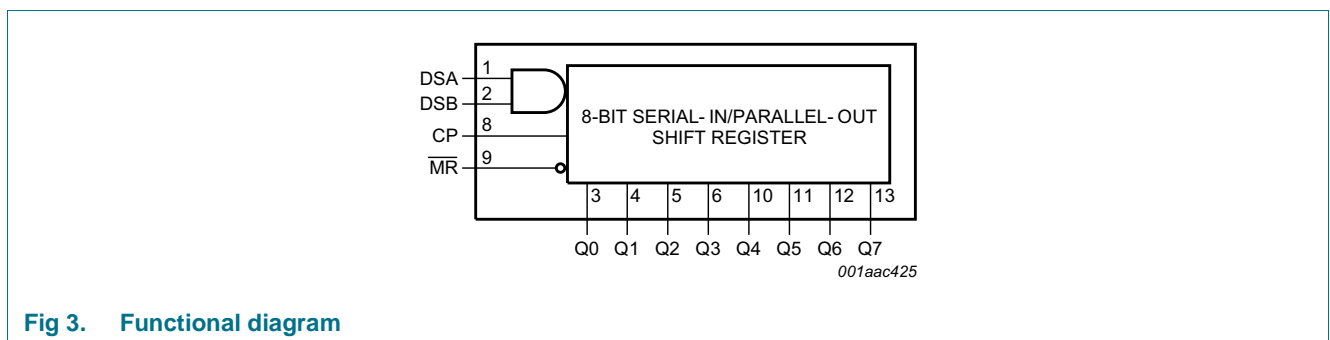
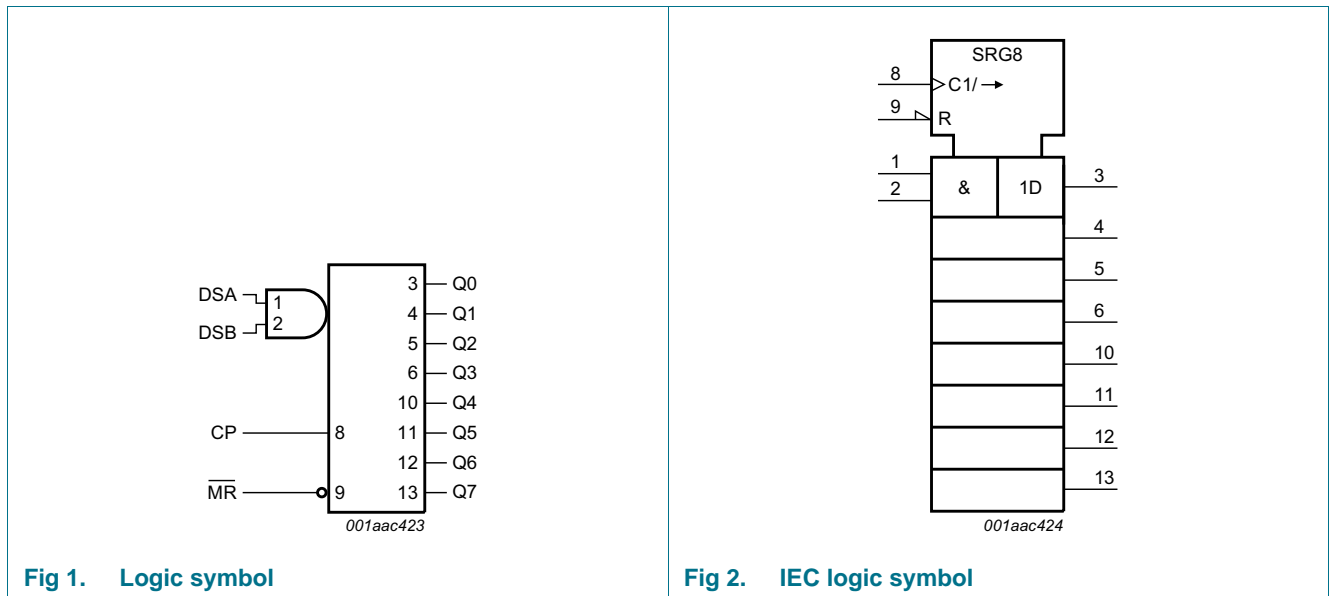


3. Ordering information

Table 1. Ordering information

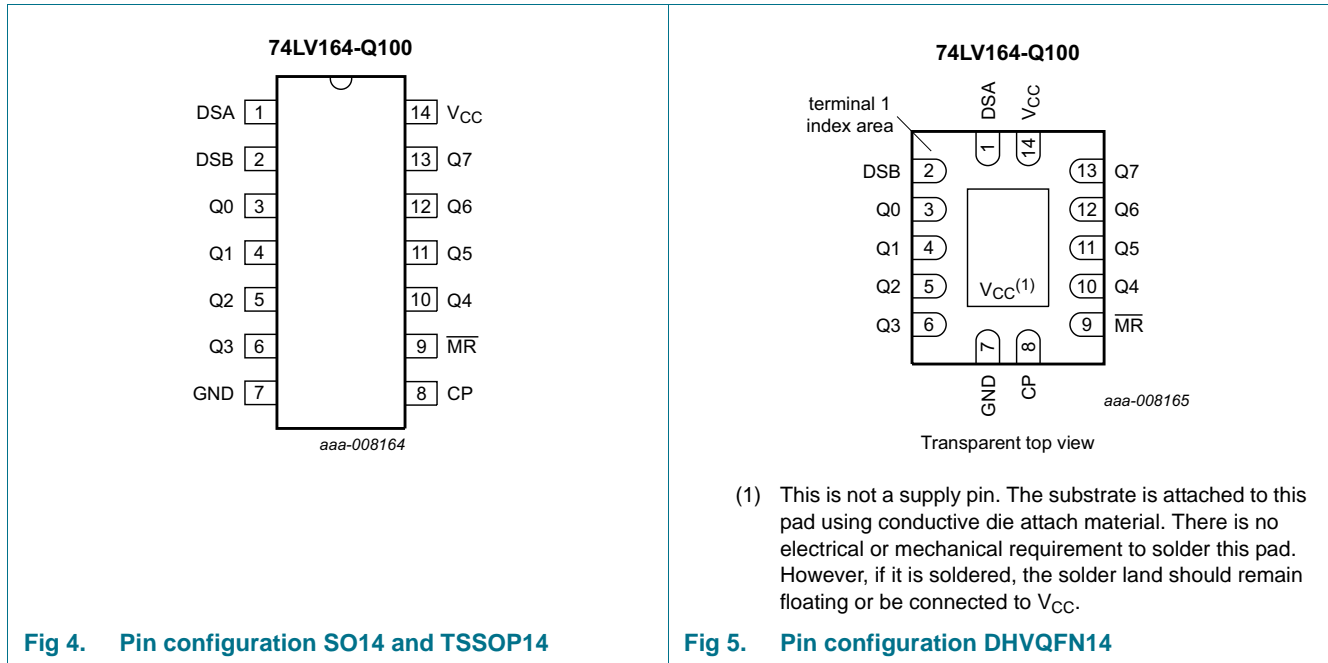
Type number	Package			Version
	Temperature range	Name	Description	
74LV164D-Q100	-40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV164PW-Q100	-40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV164BQ-Q100	-40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DSA	1	data input SA
DSB	2	data input SB
Q0	3	output 0
Q1	4	output 1
Q2	5	output 2
Q3	6	output 3
GND	7	ground (0 V)
CP	8	clock input (edge triggered LOW-to-HIGH)
$\overline{\text{MR}}$	9	master reset input (active LOW)
Q4	10	output 4
Q5	11	output 5
Q6	12	output 6
Q7	13	output 7
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Operating mode	Input				Output	
	MR	CP	DSA	DSB	Q0	Q1 to Q7
Reset (clear)	L	X	X	X	L	L to L
Shift	H	↑	l	l	L	q0 to q6
	H	↑	l	h	L	q0 to q6
	H	↑	h	l	L	q0 to q6
	H	↑	h	h	H	q0 to q6

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 ↑ = LOW-to-HIGH clock transition;
 h = HIGH voltage level one set-up time prior to the LOW-to-HIGH CP transition;
 l = LOW voltage level one set-up time prior to the LOW-to-HIGH CP transition;
 q = lower case letter indicates the state of referenced input one set-up time prior to the LOW-to-HIGH CP transition.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	±50	mA
I_O	output current	output source or sink current, $V_O = 0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	[1]	±25	mA
I_{CC}	supply current		-	±50	mA
I_{GND}	ground current		-	±50	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$	[2]	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] SO14 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 TSSOP14 package: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 DHVQFN14 package: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		[1] 1.0	3.3	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature	in free air	-40	-	+125	°C
t_r	rise time	input				
		$V_{CC} = 1.0\text{ V to }2.0\text{ V}$	-	-	500	ns/V
		$V_{CC} = 2.0\text{ V to }2.7\text{ V}$	-	-	200	ns/V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	100	ns/V
		$V_{CC} = 3.6\text{ V to }5.5\text{ V}$	-	-	50	ns/V
t_f	fall time	input				
		$V_{CC} = 1.0\text{ V to }2.0\text{ V}$	-	-	500	ns/V
		$V_{CC} = 2.0\text{ V to }2.7\text{ V}$	-	-	200	ns/V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	100	ns/V
		$V_{CC} = 3.6\text{ V to }5.5\text{ V}$	-	-	50	ns/V

[1] The static characteristics are guaranteed from $V_{CC} = 1.2\text{ V}$ to $V_{CC} = 5.5\text{ V}$. LV devices are guaranteed to function down to $V_{CC} = 1.0\text{ V}$ (with input levels GND or V_{CC}).

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1]						
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.2\text{ V}$	0.9	-	-	V
		$V_{CC} = 2.0\text{ V}$	1.4	-	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.2\text{ V}$	-	-	0.3	V
		$V_{CC} = 2.0\text{ V}$	-	-	0.6	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.8	V
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	$0.3 \times V_{CC}$	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 1.2\text{ V}$	-	1.2	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 2.0\text{ V}$	1.8	2.0	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 2.7\text{ V}$	2.5	2.7	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 3.0\text{ V}$	2.8	3.0	-	V
		$I_O = -6\text{ mA}; V_{CC} = 3.0\text{ V}$	2.4	2.82	-	V
		$I_O = -100\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	4.3	4.5	-	V
$I_O = -12\text{ mA}; V_{CC} = 4.5\text{ V}$	3.6	4.2	-	V		

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 1.2 V	-	0	-	V
		I _O = 100 μA; V _{CC} = 2.0 V	-	0	0.2	V
		I _O = 100 μA; V _{CC} = 2.7 V	-	0	0.2	V
		I _O = 100 μA; V _{CC} = 3.0 V	-	0	0.2	V
		I _O = 6 mA; V _{CC} = 3.0 V	-	0.25	0.40	V
		I _O = 100 μA; V _{CC} = 4.5 V	-	0	0.2	V
		I _O = 12 mA; V _{CC} = 4.5 V	-	0.35	0.55	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	μA
I _{CC}	supply current	quiescent: V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	20.0	μA
ΔI _{CC}	additional supply current	quiescent, per input: V _I = V _{CC} - 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	μA
C _I	input capacitance		-	3.5	-	pF
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.2 V	0.9	-	-	V
		V _{CC} = 2.0 V	1.4	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.2 V	-	-	0.3	V
		V _{CC} = 2.0 V	-	-	0.6	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	0.3 × V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 μA; V _{CC} = 1.2 V	-	-	-	V
		I _O = -100 μA; V _{CC} = 2.0 V	1.8	-	-	V
		I _O = -100 μA; V _{CC} = 2.7 V	2.5	-	-	V
		I _O = -100 μA; V _{CC} = 3.0 V	2.8	-	-	V
		I _O = -6 mA; V _{CC} = 3.0 V	2.2	-	-	V
		I _O = -100 μA; V _{CC} = 4.5 V	4.3	-	-	V
		I _O = -12 mA; V _{CC} = 4.5 V	3.5	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 μA; V _{CC} = 1.2 V	-	-	-	V
		I _O = 100 μA; V _{CC} = 2.0 V	-	-	0.2	V
		I _O = 100 μA; V _{CC} = 2.7 V	-	-	0.2	V
		I _O = 100 μA; V _{CC} = 3.0 V	-	-	0.2	V
		I _O = 6 mA; V _{CC} = 3.0 V	-	-	0.5	V
		I _O = 100 μA; V _{CC} = 4.5 V	-	-	0.2	V
		I _O = 12 mA; V _{CC} = 4.5 V	-	-	0.65	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{LI}	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	1.0	μ A
I_{CC}	supply current	quiescent: $V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	160	μ A
ΔI_{CC}	additional supply current	quiescent, per input: $V_I = V_{CC} - 0.6$ V; $V_{CC} = 2.7$ V to 3.6 V	-	-	850	μ A

[1] All typical values are measured at $T_{amb} = 25$ °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

$GND = 0$ V; $t_r = t_f \leq 2.5$ ns; $C_L = 50$ pF; $R_L = 1$ k Ω ; for test circuit, see [Figure 9](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40$ °C to $+85$ °C[1]						
t_{pd}	propagation delay	CP - see Figure 6 ; MR - see Figure 7 [2]				
		$V_{CC} = 1.2$ V	-	75	-	ns
		$V_{CC} = 2.0$ V	-	26	39	ns
		$V_{CC} = 2.7$ V	-	19	29	ns
		$V_{CC} = 3.0$ V to 3.6 V	-	14	23	ns
		$V_{CC} = 4.5$ V to 5.5 V	-	12	19	ns
		$V_{CC} = 3.0$ V to 3.6 V; $C_L = 15$ pF [3]	-	12	-	ns
t_w	pulse width	CP - see Figure 6				
		$V_{CC} = 2.0$ V	34	9	-	ns
		$V_{CC} = 2.7$ V	25	6	-	ns
		$V_{CC} = 3.0$ V to 3.6 V	20	5	-	ns
		$V_{CC} = 4.5$ V to 5.5 V	13	4	-	ns
		MR - see Figure 7				
		$V_{CC} = 2.0$ V	34	10	-	ns
		$V_{CC} = 2.7$ V	25	8	-	ns
		$V_{CC} = 3.0$ V to 3.6 V	20	6	-	ns
		$V_{CC} = 4.5$ V to 5.5 V	13	5	-	ns
t_{rem}	removal time	MR to CP - see Figure 7				
		$V_{CC} = 1.2$ V	-	30	-	ns
		$V_{CC} = 2.0$ V	19	10	-	ns
		$V_{CC} = 2.7$ V	14	8	-	ns
		$V_{CC} = 3.0$ V to 3.6 V	11	6	-	ns
		$V_{CC} = 4.5$ V to 5.5 V	8	5	-	ns

Table 7. Dynamic characteristics ...continued

GND = 0 V; $t_r = t_f \leq 2.5$ ns; $C_L = 50$ pF; $R_L = 1$ k Ω ; for test circuit, see [Figure 9](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{su}	set-up time	Dn to CP - see Figure 8				
		V _{CC} = 1.2 V	-	15	-	ns
		V _{CC} = 2.0 V	22	5	-	ns
		V _{CC} = 2.7 V	16	4	-	ns
		V _{CC} = 3.0 V to 3.6 V	13	3	-	ns
		V _{CC} = 4.5 V to 5.5 V	9	2	-	ns
t _h	hold time	Dn to CP - see Figure 8				
		V _{CC} = 1.2 V	-	-10	-	ns
		V _{CC} = 2.0 V	5	-3	-	ns
		V _{CC} = 2.7 V	5	-2	-	ns
		V _{CC} = 3.0 V to 3.6 V	5	-2	-	ns
		V _{CC} = 4.5 V to 5.5 V	5	-1	-	ns
f _{max}	maximum frequency	see Figure 6				
		V _{CC} = 2.0 V	14	40	-	MHz
		V _{CC} = 2.7 V	19	58	-	MHz
		V _{CC} = 3.0 V to 3.6 V	24	70	-	MHz
		V _{CC} = 4.5 V to 5.5 V	36	100	-	MHz
		V _{CC} = 3.3 V; C _L = 15 pF	-	78	-	MHz
C _{PD}	power dissipation capacitance	per gate: V _{CC} = 3.3 V	[4][5]	40	-	pF
T_{amb} = -40 °C to +125 °C						
t _{pd}	propagation delay	CP - see Figure 6 ; MR - see Figure 7 [2]				
		V _{CC} = 1.2 V	-	-	-	ns
		V _{CC} = 2.0 V	-	-	49	ns
		V _{CC} = 2.7 V	-	-	36	ns
		V _{CC} = 3.0 V to 3.6 V	-	-	29	ns
		V _{CC} = 4.5 V to 5.5 V	-	-	24	ns
t _w	pulse width	CP - see Figure 6 ; MR - see Figure 7				
		V _{CC} = 2.0 V	41	-	-	ns
		V _{CC} = 2.7 V	30	-	-	ns
		V _{CC} = 3.0 V to 3.6 V	24	-	-	ns
		V _{CC} = 4.5 V to 5.5 V	16	-	-	ns
t _{rem}	removal time	MR to CP - see Figure 7				
		V _{CC} = 1.2 V	-	-	-	ns
		V _{CC} = 2.0 V	24	-	-	ns
		V _{CC} = 2.7 V	18	-	-	ns
		V _{CC} = 3.0 V to 3.6 V	14	-	-	ns
		V _{CC} = 4.5 V to 5.5 V	10	-	-	ns

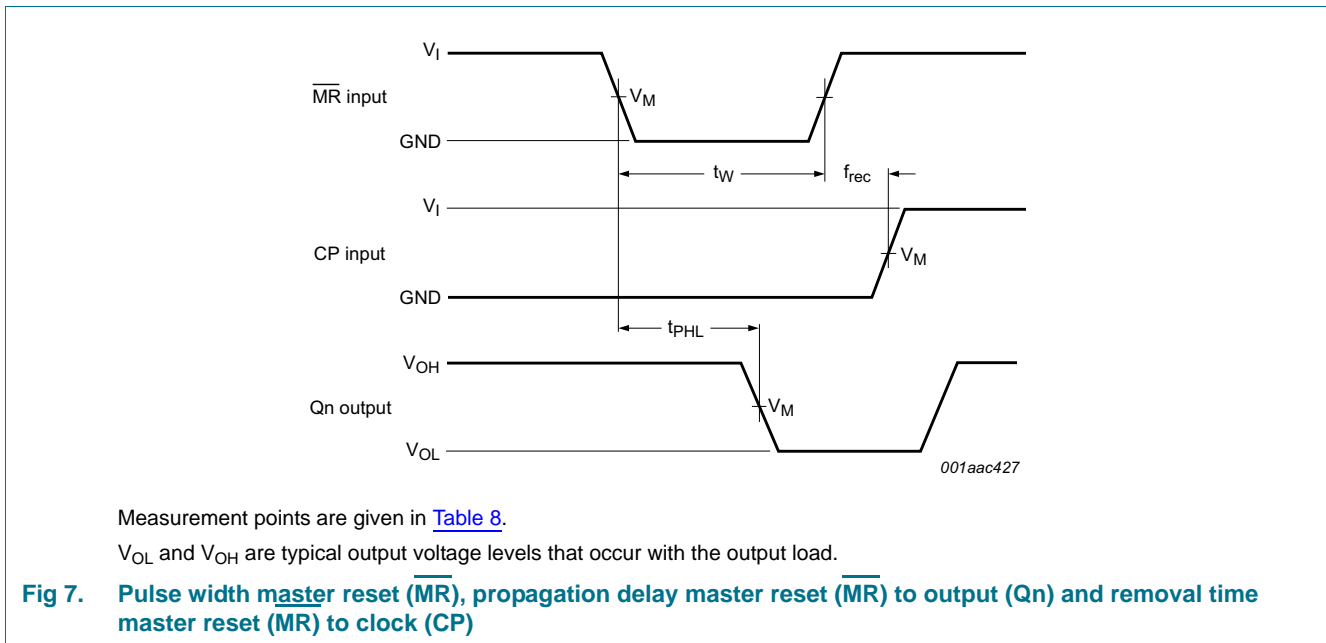
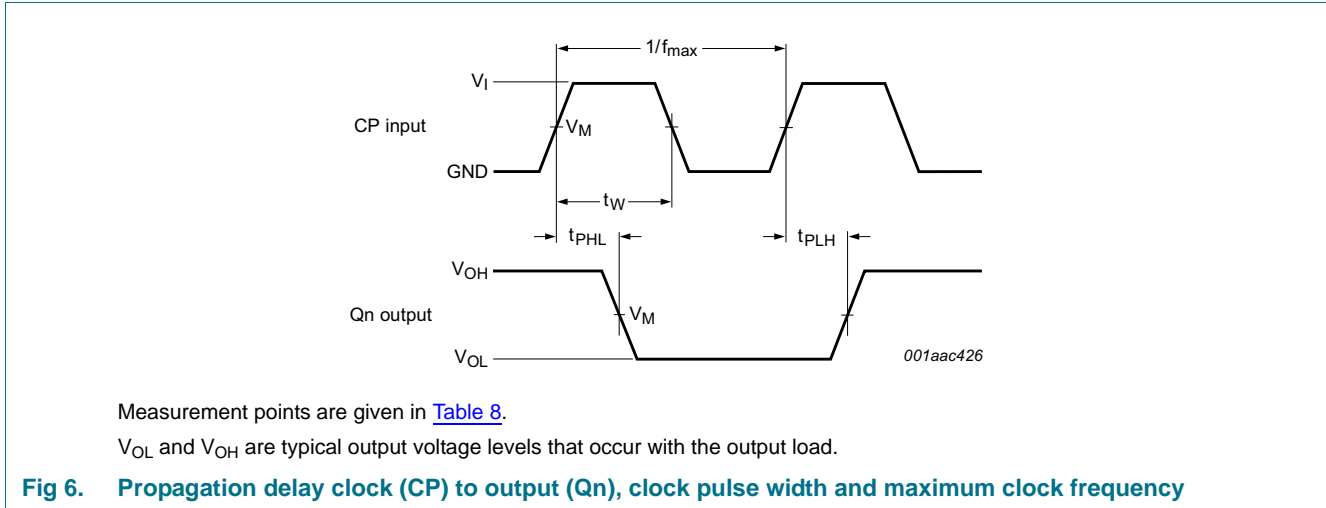
Table 7. Dynamic characteristics ...continued

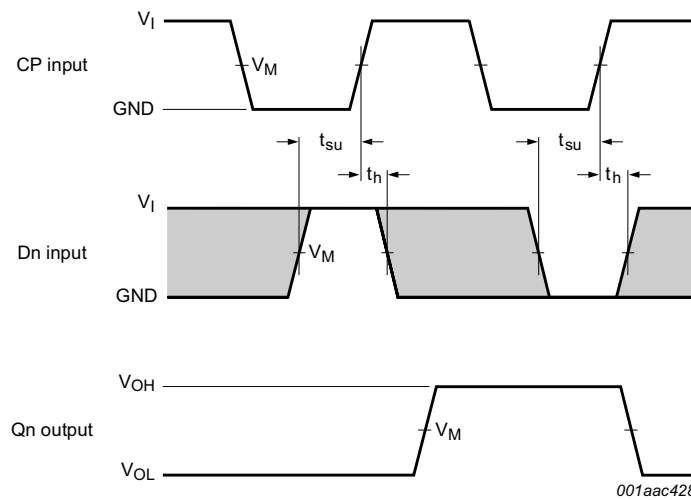
$GND = 0\text{ V}$; $t_r = t_f \leq 2.5\text{ ns}$; $C_L = 50\text{ pF}$; $R_L = 1\text{ k}\Omega$; for test circuit, see [Figure 9](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{su}	set-up time	Dn to CP - see Figure 8				
		V _{CC} = 1.2 V	-	-	-	ns
		V _{CC} = 2.0 V	26	-	-	ns
		V _{CC} = 2.7 V	19	-	-	ns
		V _{CC} = 3.0 V to 3.6 V	15	-	-	ns
		V _{CC} = 4.5 V to 5.5 V	10	-	-	ns
t _h	hold time	Dn to CP - see Figure 8				
		V _{CC} = 1.2 V	-	-	-	ns
		V _{CC} = 2.0 V	5	-	-	ns
		V _{CC} = 2.7 V	5	-	-	ns
		V _{CC} = 3.0 V to 3.6 V	5	-	-	ns
		V _{CC} = 4.5 V to 5.5 V	5	-	-	ns
f _{max}	maximum frequency	see Figure 6				
		V _{CC} = 2.0 V	12	-	-	MHz
		V _{CC} = 2.7 V	16	-	-	MHz
		V _{CC} = 3.0 V to 3.6 V	20	-	-	MHz
		V _{CC} = 4.5 V to 5.5 V	30	-	-	MHz

- [1] Typical values are measured at nominal V_{CC} and T_{amb} = 25 °C.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V).
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 Σ(C_L × V_{CC}² × f_o) = sum of the outputs.
- [5] The condition is V_I = GND to V_{CC}.

11. Waveforms



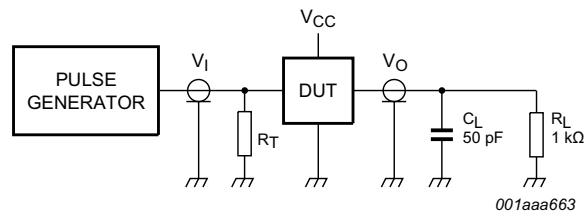


Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.
 The shaded areas indicate when the input is permitted to change for predictable output performance.

Fig 8. Data set-up and hold times inputs (Dn) to clock (CP)

Table 8. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.2 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.0 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in [Table 9](#).

Definitions for test circuit:

R_L = Load resistor.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

Fig 9. Test circuit for measuring switching times

Table 9. Test data

Supply voltage	Input		Load		Test
V_{CC}	V_I	t_r, t_f	C_L	R_L	
1.2 V	V_{CC}	≤ 2.5 ns	50 pF	1 k Ω	t_{PHL}, t_{PLH}
2.0 V	V_{CC}	≤ 2.5 ns	50 pF	1 k Ω	t_{PHL}, t_{PLH}
2.7 V	2.7 V	≤ 2.5 ns	50 pF	1 k Ω	t_{PHL}, t_{PLH}
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF, 15 pF	1 k Ω	t_{PHL}, t_{PLH}
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	1 k Ω	t_{PHL}, t_{PLH}

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

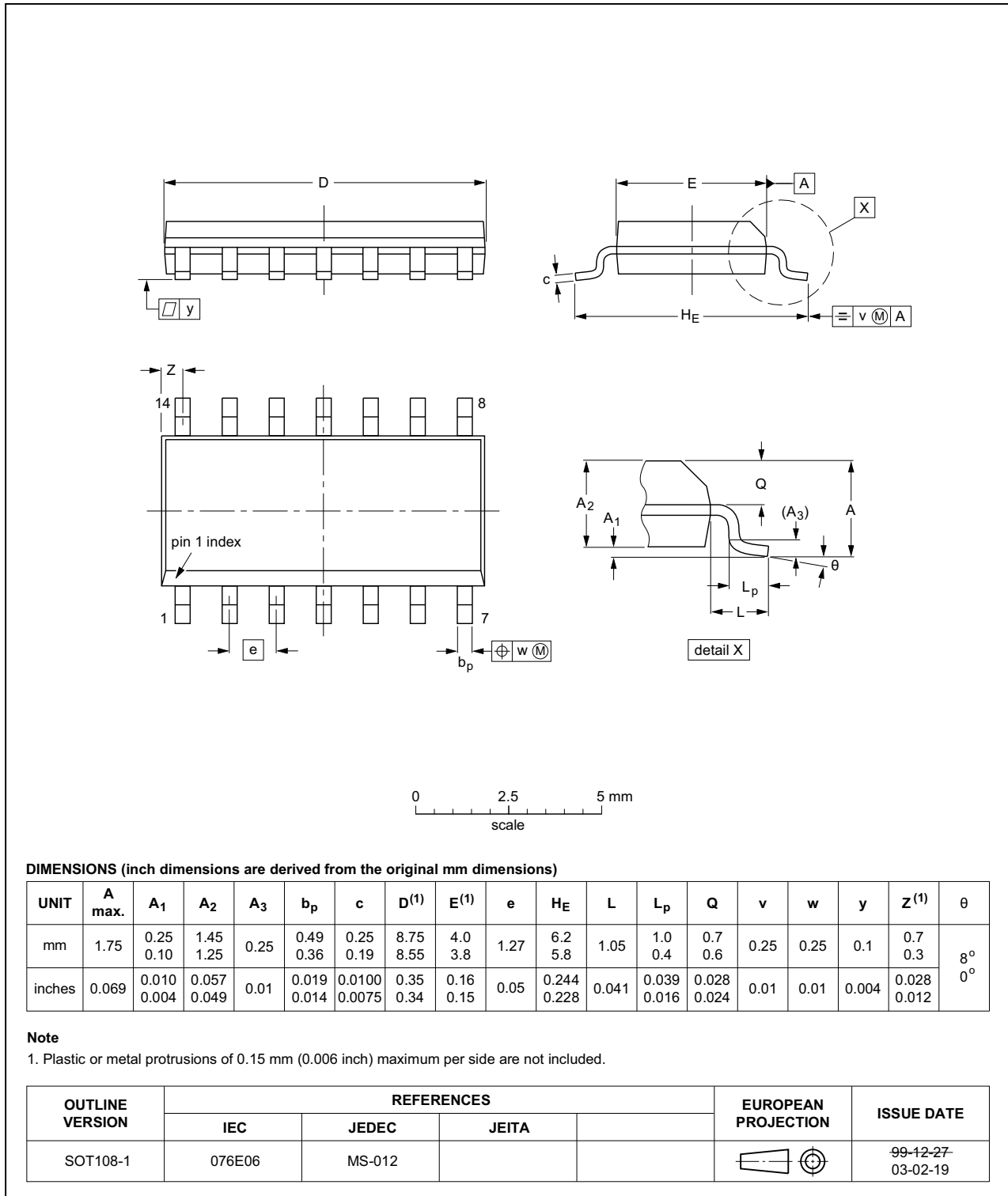


Fig 10. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

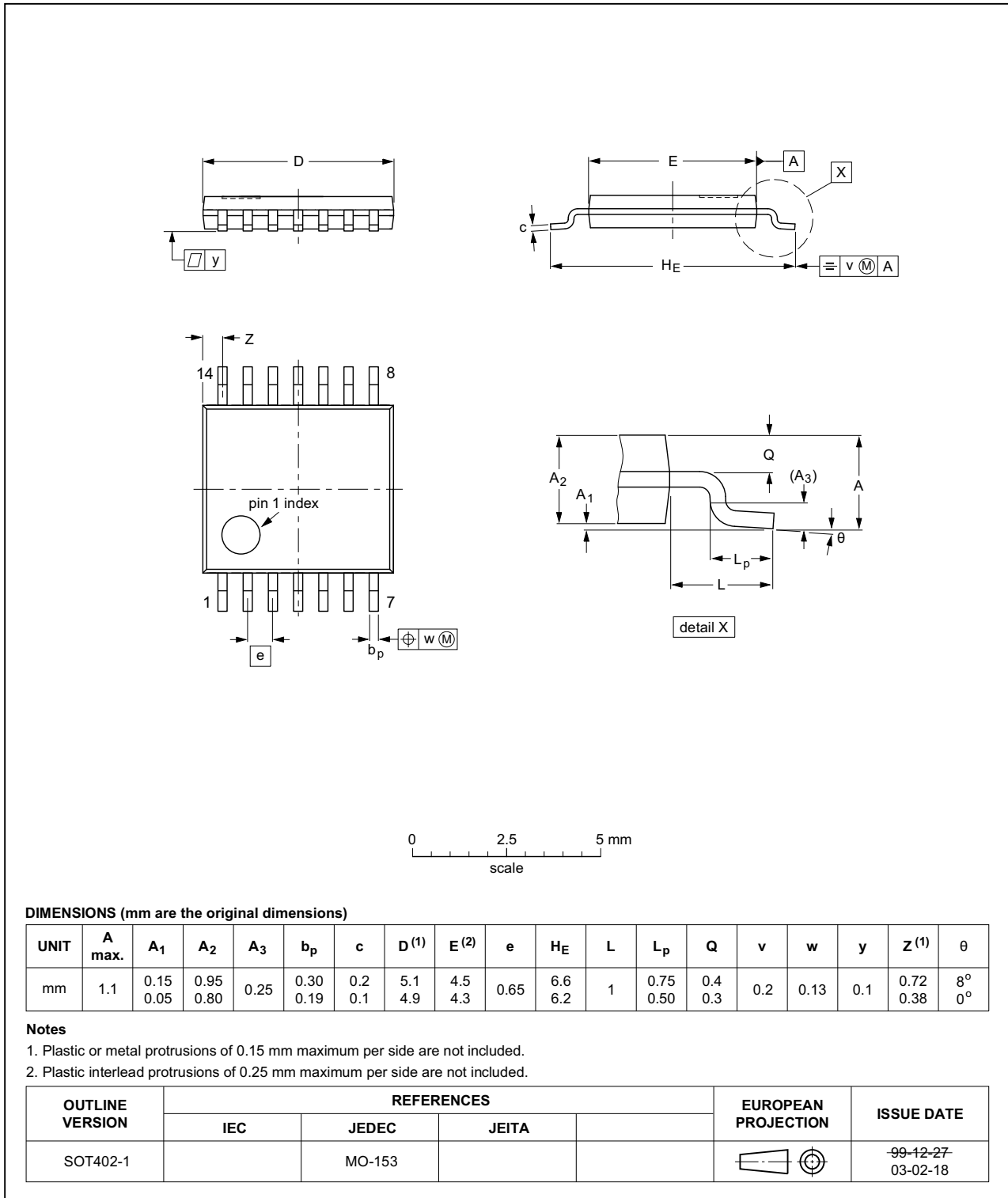


Fig 11. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

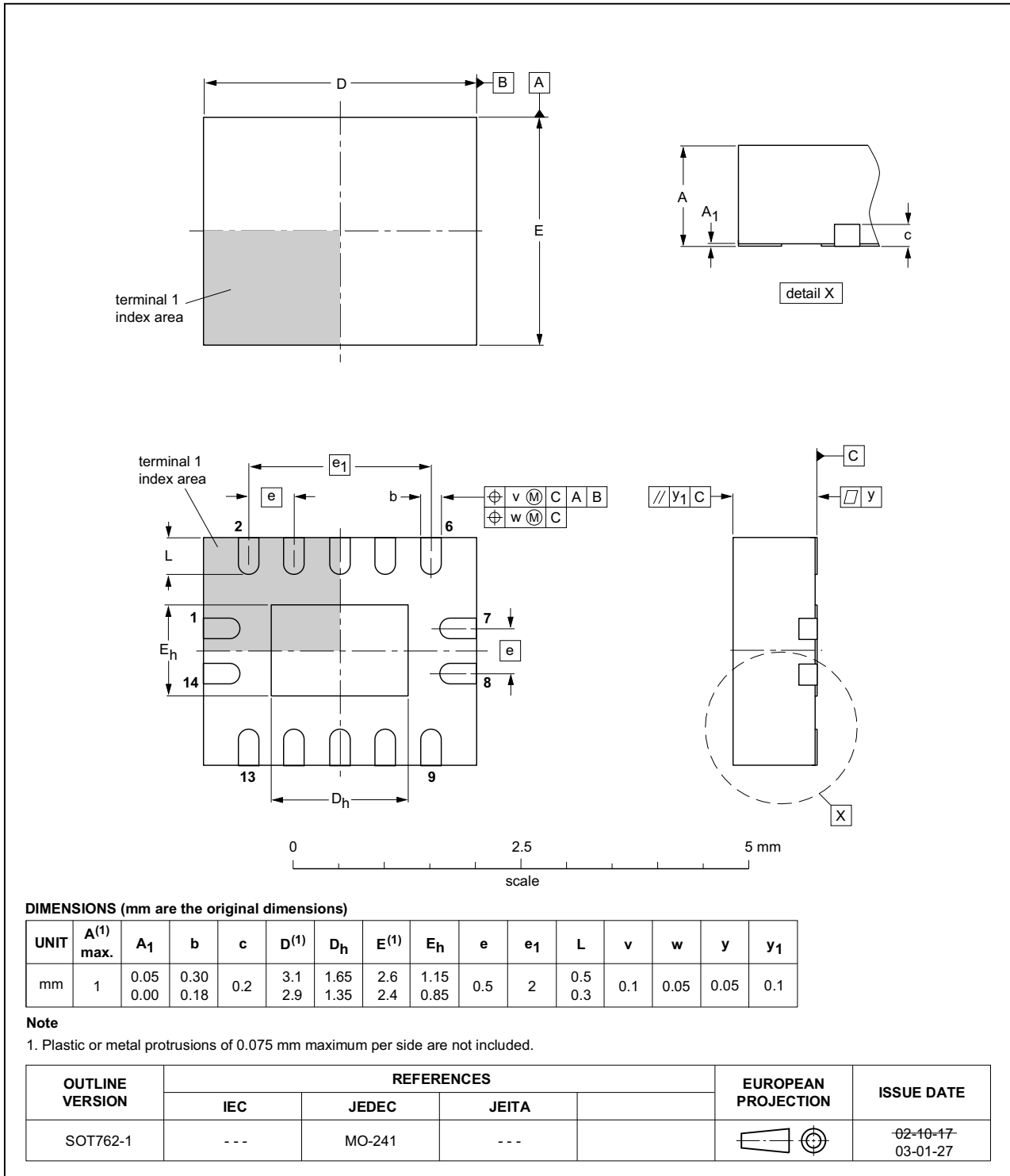


Fig 12. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV164_Q100 v.2	20140918	Product data sheet	-	74LV164_Q100 v.1
Modifications:	• Section 2 : ESD protection: MIL-STD-833 changed to MIL-STD883			
74LV164_Q100 v.1	20130626	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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